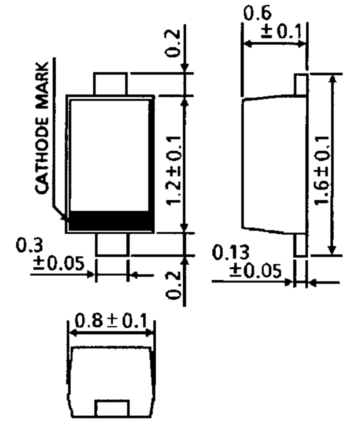
TOSHIBA Diode Silicon Epitaxial Planar Type

JDV2S01E

VCO for UHF band

- Small Package
- High Capacitance Ratio: C_{1V}/C_{4V} = 2.0 (typ.)
- Low Series Resistance: r_s = 0.5 Ω (typ.)

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	1-1G1A

Weight: 0.0014 g

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	I_R = 1 μA	10	—	—	V
Reverse current	I_R	V_R = 10 V	—	—	3	nA
Capacitance	C_{1V}	V_R = 1 V, f = 1 MHz	2.85	3.15	3.45	pF
	C_{4V}	V_R = 4 V, f = 1 MHz	1.35	1.57	1.81	
Capacitance ratio	C_{1V}/C_{4V}	—	1.8	2	—	—
Series resistance	r_s	V_R = 1 V, f = 470 MHz	—	0.5	0.7	Ω

Note: Signal level when capacitance is measured. V_{sig} = 100 mV_{rms}

Marking